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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Active
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	266MHz
Co-Processors/DSP	Communications; QUICC Engine
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (1)
SATA	-
USB	USB 1.x (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	740-LBGA
Supplier Device Package	740-TBGA (37.5x37.5)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mpc8358vvaddea

2.1 Overall DC Electrical Characteristics

This section covers the ratings, conditions, and other characteristics.

2.1.1 Absolute Maximum Ratings

This table provides the absolute maximum ratings.

Table 1. Absolute Maximum Ratings[1]

Characteristic		Symbol	Max Value	Unit	Notes
Core and PLL supply voltage for MPC8358 Device Part Number with Processor Frequency label of AD=266MHz and AG=400MHz & QUICC Engine Frequency label of E=300MHz & G=400MHz MPC8360 Device Part Number with Processor Frequency label of AG=400MHz and AJ=533MHz & QUICC Engine Frequency label of G=400MHz		V_{DD} & AV_{DD}	–0.3 to 1.32	V	—
Core and PLL supply voltage for MPC8360 device Part Number with Processor Frequency label of AL=667MHz and QUICC Engine Frequency label of H=500MHz		V_{DD} & AV_{DD}	–0.3 to 1.37	V	—
DDR and DDR2 DRAM I/O voltage DDR DDR2		GV_{DD}	 –0.3 to 2.75 –0.3 to 1.89	V	—
Three-speed Ethernet I/O, MII management voltage		LV_{DD}	–0.3 to 3.63	V	—
PCI, local bus, DUART, system control and power management, I^2C, SPI, and JTAG I/O voltage		OV_{DD}	–0.3 to 3.63	V	—
Input voltage	DDR DRAM signals	MV_{IN}	–0.3 to (GV_{DD} + 0.3)	V	2, 5
	DDR DRAM reference	MV_{REF}	–0.3 to (GV_{DD} + 0.3)	V	2, 5
	Three-speed Ethernet signals	LV_{IN}	–0.3 to (LV_{DD} + 0.3)	V	4, 5
	Local bus, DUART, CLKIN, system control and power management, I^2C, SPI, and JTAG signals	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	3, 5
	PCI	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	6

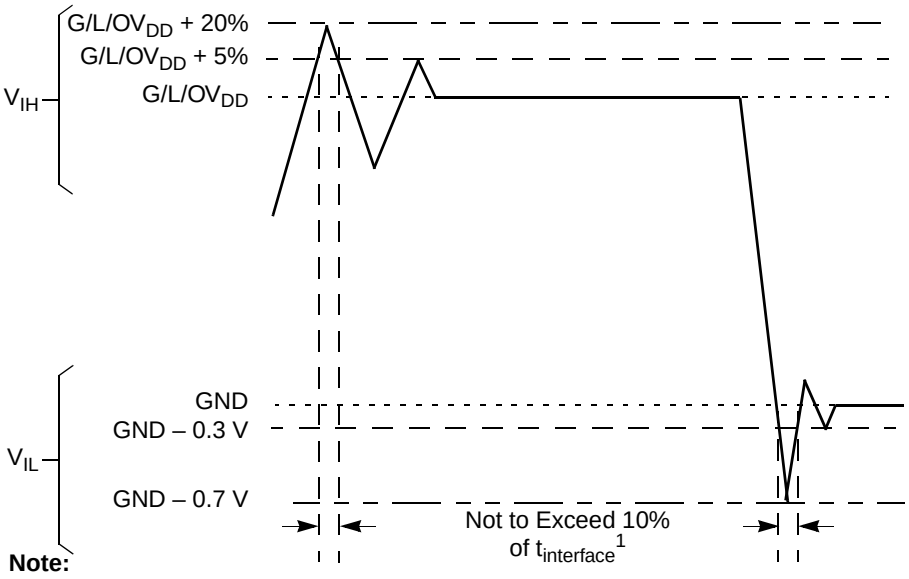
Table 2. Recommended Operating Conditions (continued)

Characteristic	Symbol	Recommended Value	Unit	Notes
PCI, local bus, DUART, system control and power management, I^2C, SPI, and JTAG I/O voltage	OV_{DD}	3.3 V ± 330 mV	V	—
Junction temperature	T_J	0 to 105 –40 to 105	°C	2

Notes:

1. GV_{DD}, LV_{DD}, OV_{DD}, AV_{DD}, and V_{DD} must track each other and must vary in the same direction—either in the positive or negative direction.
2. The operating conditions for junction temperature, T_J, on the 600/333/400 MHz and 500/333/500 MHz on rev. 2.0 silicon is 0° to 70 °C. Refer to Errata General9 in *Chip Errata for the MPC8360E, Rev. 1*.
3. For more information on Part Numbering, refer to Table 80.

This figure shows the undershoot and overshoot voltages at the interfaces of the device.



Note:
1. Note that $t_{interface}$ refers to the clock period associated with the bus clock interface.

Figure 3. Overshoot/Undershoot Voltage for $GV_{DD}/OV_{DD}/LV_{DD}$

2.2.1 Power-Up Sequencing

MPC8360E/58E does not require the core supply voltage (V_{DD} and AV_{DD}) and I/O supply voltages (GV_{DD}, LV_{DD}, and OV_{DD}) to be applied in any particular order. During the power ramp up, before the power supplies are stable and if the I/O voltages are supplied before the core voltage, there may be a period of time that all input and output pins are actively be driven and cause contention and excessive current from 3A to 5A. In order to avoid actively driving the I/O pins and to eliminate excessive current draw, apply the core voltage (V_{DD}) before the I/O voltage (GV_{DD}, LV_{DD}, and OV_{DD}) and assert $\overline{\text{PORESET}}$ before the power supplies fully ramp up. In the case where the core voltage is applied first, the core voltage supply must rise to 90% of its nominal value before the I/O supplies reach 0.7 V, see this figure.

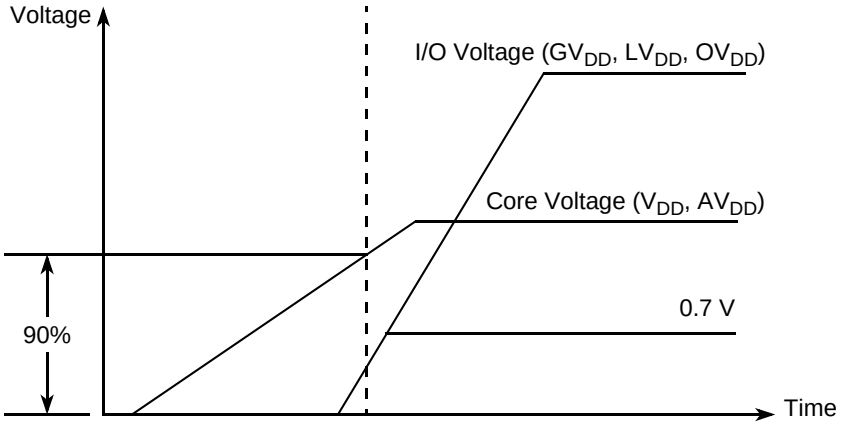


Figure 5. Power Sequencing Example

I/O voltage supplies (GV_{DD}, LV_{DD}, and OV_{DD}) do not have any ordering requirements with respect to one another.

2.2.2 Power-Down Sequencing

The MPC8360E/58E does not require the core supply voltage and I/O supply voltages to be powered down in any particular order.

3 Power Characteristics

The estimated typical power dissipation values are shown in these tables.

Table 4. MPC8360E TBGA Core Power Dissipation[1]

Core Frequency (MHz)	CSB Frequency (MHz)	QUICC Engine Frequency (MHz)	Typical	Maximum	Unit	Notes
266	266	500	5.0	5.6	W	2, 3, 5
400	266	400	4.5	5.0	W	2, 3, 4
533	266	400	4.8	5.3	W	2, 3, 4
667	333	400	5.8	6.3	W	3, 6, 7, 8
500	333	500	5.9	6.4	W	3, 6, 7, 8

Table 4. MPC8360E TBGA Core Power Dissipation[1] (continued)

Core Frequency (MHz)	CSB Frequency (MHz)	QUICC Engine Frequency (MHz)	Typical	Maximum	Unit	Notes
667	333	500	6.1	6.8	W	2, 3, 5, 9

Notes:
1. The values do not include I/O supply power (OV_{DD}, LV_{DD}, GV_{DD}) or AV_{DD}. For I/O power values, see Table 6.
2. Typical power is based on a voltage of V_{DD} = 1.2 V or 1.3 V, a junction temperature of T_J = 105° C, and a Dhrystone benchmark application.
3. Thermal solutions need to design to a value higher than typical power on the end application, T_A target, and I/O power.
4. Maximum power is based on a voltage of V_{DD} = 1.2 V, WC process, a junction T_J = 105° C, and an artificial smoke test.
5. Maximum power is based on a voltage of V_{DD} = 1.3 V for applications that use 667 MHz (CPU)/500 (QE) with WC process, a junction T_J = 105° C, and an artificial smoke test.
6. Typical power is based on a voltage of V_{DD} = 1.3 V, a junction temperature of T_J = 70° C, and a Dhrystone benchmark application.
7. Maximum power is based on a voltage of V_{DD} = 1.3 V for applications that use 667 MHz (CPU) or 500 (QE) with WC process, a junction T_J = 70° C, and an artificial smoke test.
8. This frequency combination is only available for rev. 2.0 silicon.
9. This frequency combination is not available for rev. 2.0 silicon.

Table 5. MPC8358E TBGA Core Power Dissipation[1]

Core Frequency (MHz)	CSB Frequency (MHz)	QUICC Engine Frequency (MHz)	Typical	Maximum	Unit	Notes
266	266	300	4.1	4.5	W	2, 3, 4
400	266	400	4.5	5.0	W	2, 3, 4

Notes:
1. The values do not include I/O supply power (OV_{DD}, LV_{DD}, GV_{DD}) or AV_{DD}. For I/O power values, see Table 6.
2. Typical power is based on a voltage of V_{DD} = 1.2 V, a junction temperature of T_J = 105° C, and a Dhrystone benchmark application.
3. Thermal solutions need to design to a value higher than typical power on the end application, T_A target, and I/O power.
4. Maximum power is based on a voltage of V_{DD} = 1.2 V, WC process, a junction T_J = 105° C, and an artificial smoke test.

6.1 DDR and DDR2 SDRAM DC Electrical Characteristics

This table provides the recommended operating conditions for the DDR2 SDRAM component(s) of the device when GV_{DD}(typ) = 1.8 V.

Table 14. DDR2 SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	1.71	1.89	V	1
I/O reference voltage	MV_{REF}	0.49 × GV_{DD}	0.51 × GV_{DD}	V	2
I/O termination voltage	V_{TT}	MV_{REF} – 0.04	MV_{REF} + 0.04	V	3
Input high voltage	V_{IH}	MV_{REF} + 0.125	GV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	MV_{REF} – 0.125	V	—
Output leakage current	I_{OZ}	—	±10	µA	4
Output high current (V_{OUT} = 1.420 V)	I_{OH}	–13.4	—	mA	—
Output low current (V_{OUT} = 0.280 V)	I_{OL}	13.4	—	mA	—
MV_{REF} input leakage current	I_{VREF}	—	±10	µA	—
Input current (0 V ≤ V_{IN} ≤ GV_{DD})	I_{IN}	—	±10	µA	—

Notes:

1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. MV_{REF} is expected to equal 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} cannot exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to equal MV_{REF}. This rail should track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ GV_{DD}.

This table provides the DDR2 capacitance when GV_{DD}(typ) = 1.8 V.

Table 15. DDR2 SDRAM Capacitance for GV_{DD}(typ)=1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{DIO}	—	0.5	pF	1

Note:

1. This parameter is sampled. GV_{DD} = 1.8 V ± 0.090 V, f = 1 MHz, T_A = 25°C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.2 V.

This table provides the recommended operating conditions for the DDR SDRAM component(s) of the device when GV_{DD}(typ) = 2.5 V.

Table 16. DDR SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	2.375	2.625	V	1
I/O reference voltage	MV_{REF}	0.49 × GV_{DD}	0.51 × GV_{DD}	V	2
I/O termination voltage	V_{TT}	MV_{REF} – 0.04	MV_{REF} + 0.04	V	3

Table 21. DDR and DDR2 SDRAM Output AC Timing Specifications for Source Synchronous Mode (continued)

At recommended operating conditions with GV_{DD} of (1.8 V or 2.5 V) ± 5%.

Parameter[8]	Symbol[1]	Min	Max	Unit	Notes
MDQS epilogue end	t_{DDKHME}	–0.6	0.9	ns	7

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
2. All MCK/$\overline{\text{MCK}}$ referenced measurements are made from the crossing of the two signals ±0.1 V.
3. In the source synchronous mode, MCK/$\overline{\text{MCK}}$ can be shifted in ¼ applied cycle increments through the clock control register. For the skew measurements referenced for t_{AOSKEW} it is assumed that the clock adjustment is set to align the address/command valid with the rising edge of MCK.
4. ADDR/CMD includes all DDR SDRAM output signals except MCK/$\overline{\text{MCK}}$, $\overline{\text{MCS}}$, and MDQ/MECC/MDM/MDQS. For the ADDR/CMD setup and hold specifications, it is assumed that the clock control register is set to adjust the memory clocks by ½ applied cycle.
5. Note that t_{DDKHMH} follows the symbol conventions described in note 1. For example, t_{DDKHMH} describes the DDR timing (DD) from the rising edge of the MCK(n) clock (KH) until the MDQS signal is valid (MH). t_{DDKHMH} can be modified through control of the DQSS override bits in the TIMING_CFG_2 register. In source synchronous mode, this is typically set to the same delay as the clock adjust in the CLK_CNTL register. The timing parameters listed in the table assume that these two parameters have been set to the same adjustment value. Refer *MPC8360E PowerQUICC II Pro Integrated Communications Processor Reference Manual* for a description and understanding of the timing modifications enabled by use of these bits.
6. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe should be centered inside of the data eye at the pins of the device.
7. All outputs are referenced to the rising edge of MCK(n) at the pins of the device. Note that t_{DDKHMP} follows the symbol conventions described in note 1.
8. AC timing values are based on the DDR data rate, which is twice the DDR memory bus frequency.
9. In rev. 2.0 silicon, t_{DDKHMH} maximum meets the specification of 0.6 ns. In rev. 2.0 silicon, due to errata, t_{DDKHMH} minimum is –0.9 ns. Refer to Errata DDR18 in *Chip Errata for the MPC8360E, Rev. 1*.

This figure shows the DDR SDRAM output timing for address skew with respect to any MCK.

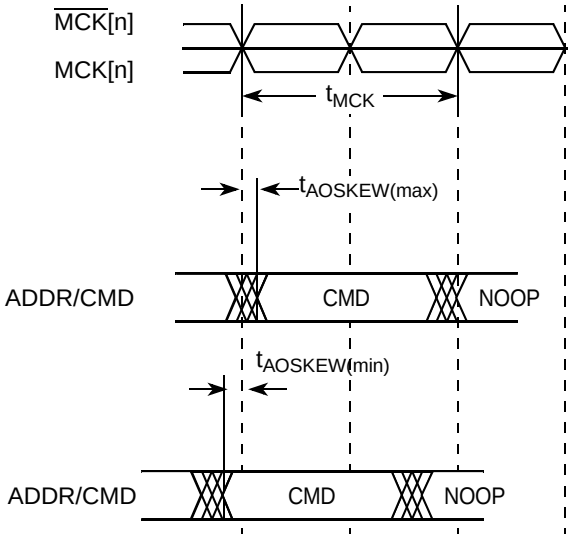


Figure 7. Timing Diagram for t_{AOSKEW} Measurement

8.2.1.2 GMII Receive AC Timing Specifications

This table provides the GMII receive AC timing specifications.

Table 28. GMII Receive AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit	Notes
RX_CLK clock period	t_{GRX}	—	8.0	—	ns	—
RX_CLK duty cycle	t_{GRXH}/t_{GRX}	40	—	60	%	—
RXD[7:0], RX_DV, RX_ER setup time to RX_CLK	t_{GRDVKH}	2.0	—	—	ns	—
RXD[7:0], RX_DV, RX_ER hold time to RX_CLK	t_{GRDXKH}	0.2	—	—	ns	2
RX_CLK clock rise time, (20% to 80%)	t_{GRXR}	—	—	1.0	ns	—
RX_CLK clock fall time, (80% to 20%)	t_{GRXF}	—	—	1.0	ns	—

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{GRDVKH} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{RX} clock reference (K) going to the high state (H) or setup time. Also, t_{GRDXKL} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{GRX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{GRX} represents the GMII (G) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. In rev. 2.0 silicon, due to errata, t_{GRDXKH} minimum is 0.5 which is not compliant with the standard. Refer to Errata *QE_ENET18* in *Chip Errata for the MPC8360E, Rev. 1*.

This figure shows the GMII receive AC timing diagram.

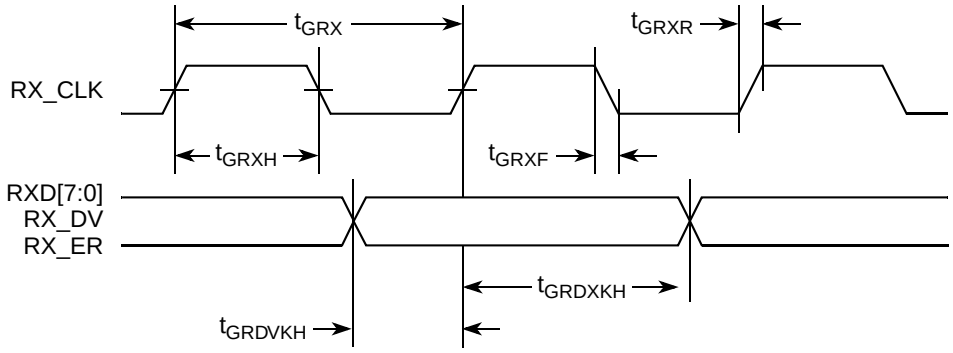


Figure 11. GMII Receive AC Timing Diagram

8.2.2.2 MII Receive AC Timing Specifications

This table provides the MII receive AC timing specifications.

Table 30. MII Receive AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
RX_CLK clock period 10 Mbps	t_{MRX}	—	400	—	ns
RX_CLK clock period 100 Mbps	t_{MRX}	—	40	—	ns
RX_CLK duty cycle	t_{MRXH}/t_{MRX}	35	—	65	%
RXD[3:0], RX_DV, RX_ER setup time to RX_CLK	t_{MRDVKH}	10.0	—	—	ns
RXD[3:0], RX_DV, RX_ER hold time to RX_CLK	t_{MRDXKH}	10.0	—	—	ns
RX_CLK clock rise time, (20% to 80%)	t_{MRXR}	1.0	—	4.0	ns
RX_CLK clock fall time, (80% to 20%)	t_{MRXF}	1.0	—	4.0	ns

Note:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MRDVKH} symbolizes MII receive timing (MR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MRX} clock reference (K) going to the high (H) state or setup time. Also, t_{MRDXKL} symbolizes MII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{MRX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{MRX} represents the MII (M) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

This figure provides the AC test load.

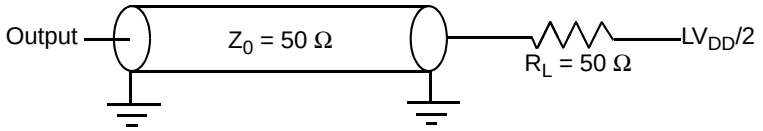


Figure 13. AC Test Load

This figure shows the MII receive AC timing diagram.

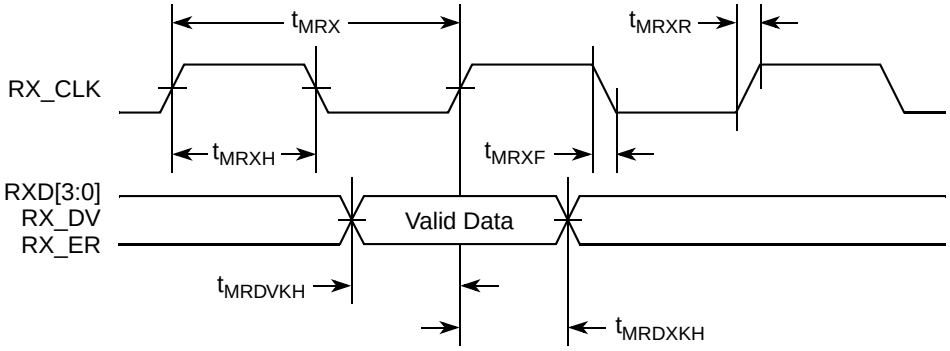


Figure 14. MII Receive AC Timing Diagram

8.2.4.1 TBI Transmit AC Timing Specifications

This table provides the TBI transmit AC timing specifications.

Table 33. TBI Transmit AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit	Notes
GTX_CLK clock period	t_{TTX}	—	8.0	—	ns	—
GTX_CLK duty cycle	t_{TTXH}/t_{TTX}	40	—	60	%	—
GTX_CLK to TBI data TCG[9:0] delay	t_{TTKHDX} t_{TTKHDV}	1.0 —	—	— 5.0	ns	3
GTX_CLK clock rise time, (20% to 80%)	t_{TTXR}	—	—	1.0	ns	—
GTX_CLK clock fall time, (80% to 20%)	t_{TTXF}	—	—	1.0	ns	—
GTX_CLK125 reference clock period	t_{G125}	—	8.0	—	ns	2
GTX_CLK125 reference clock duty cycle	t_{G125H}/t_{G125}	45	—	55	ns	—

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{TTKHDV} symbolizes the TBI transmit timing (TT) with respect to the time from t_{TTX} (K) going high (H) until the referenced data signals (D) reach the valid state (V) or setup time. Also, t_{TTKHDX} symbolizes the TBI transmit timing (TT) with respect to the time from t_{TTX} (K) going high (H) until the referenced data signals (D) reach the invalid state (X) or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{TTX} represents the TBI (T) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. This symbol is used to represent the external GTX_CLK125 and does not follow the original symbol naming convention.
3. In rev. 2.0 silicon, due to errata, t_{TTKHDX} minimum is 0.7 ns for UCC1. Refer to Errata *QE_ENET19* in *Chip Errata for the MPC8360E, Rev. 1*.

This figure shows the TBI transmit AC timing diagram.

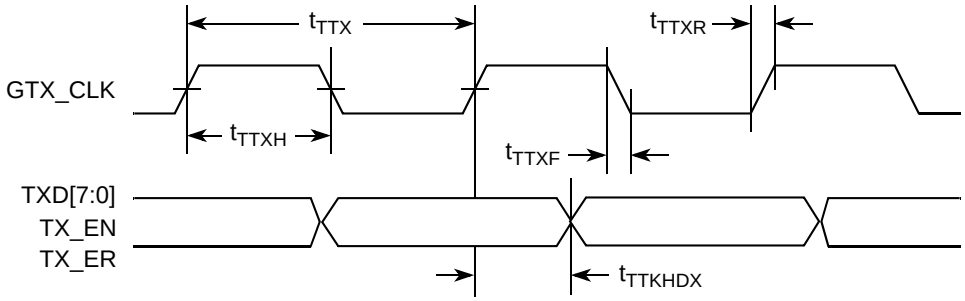


Figure 18. TBI Transmit AC Timing Diagram

8.3.2 MII Management AC Electrical Specifications

This table provides the MII management AC timing specifications.

Table 37. MII Management AC Timing Specifications

At recommended operating conditions with LV_{DD} is 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit	Notes
MDC frequency	f_{MDC}	—	2.5	—	MHz	2
MDC period	t_{MDC}	—	400	—	ns	—
MDC clock pulse width high	t_{MDCH}	32	—	—	ns	—
MDC to MDIO delay	$t_{MDTKHDX}$ $t_{MDTKHDV}$	10 —	—	— 110	ns	3
MDIO to MDC setup time	$t_{MDRDVKH}$	10	—	—	ns	—
MDIO to MDC hold time	$t_{MDRDXKH}$	0	—	—	ns	—
MDC rise time	t_{MDCR}	—	—	10	ns	—
MDC fall time	t_{MDHF}	—	—	10	ns	—

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MDKHDX} symbolizes management data timing (MD) for the time t_{MDC} from clock reference (K) high (H) until data outputs (D) are invalid (X) or data hold time. Also, $t_{MDRDVKH}$ symbolizes management data timing (MD) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MDC} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. This parameter is dependent on the csb_clk speed (that is, for a csb_clk of 267 MHz, the maximum frequency is 8.3 MHz and the minimum frequency is 1.2 MHz; for a csb_clk of 375 MHz, the maximum frequency is 11.7 MHz and the minimum frequency is 1.7 MHz).
3. This parameter is dependent on the ce_clk speed (that is, for a ce_clk of 200 MHz, the delay is 90 ns and for a ce_clk of 300 MHz, the delay is 63 ns).

This figure shows the MII management AC timing diagram.

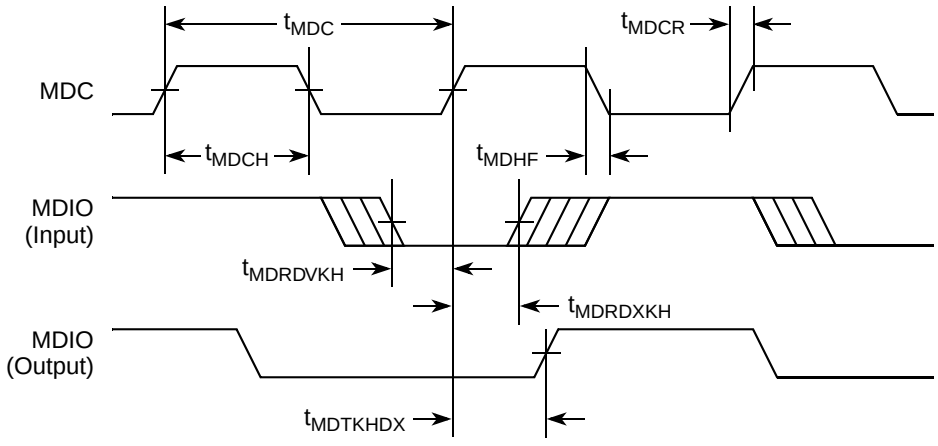


Figure 21. MII Management Interface Timing Diagram

These figures show the local bus signals.

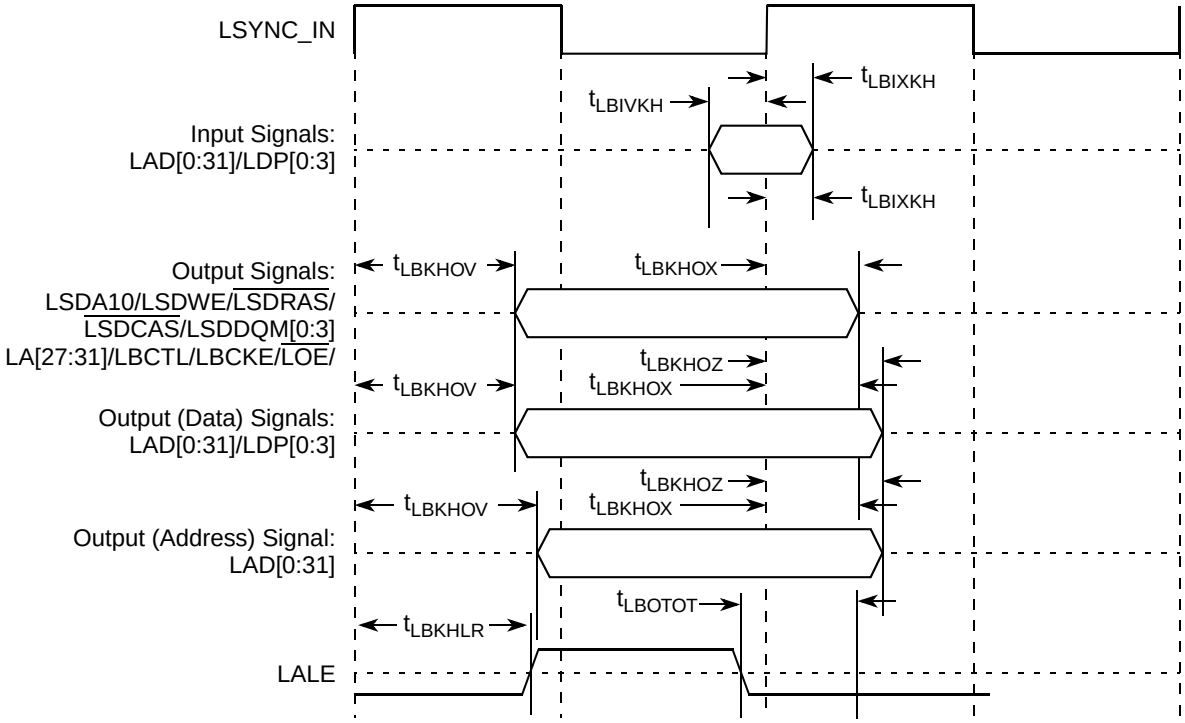


Figure 23. Local Bus Signals, Nonspecial Signals Only (DLL Enabled)

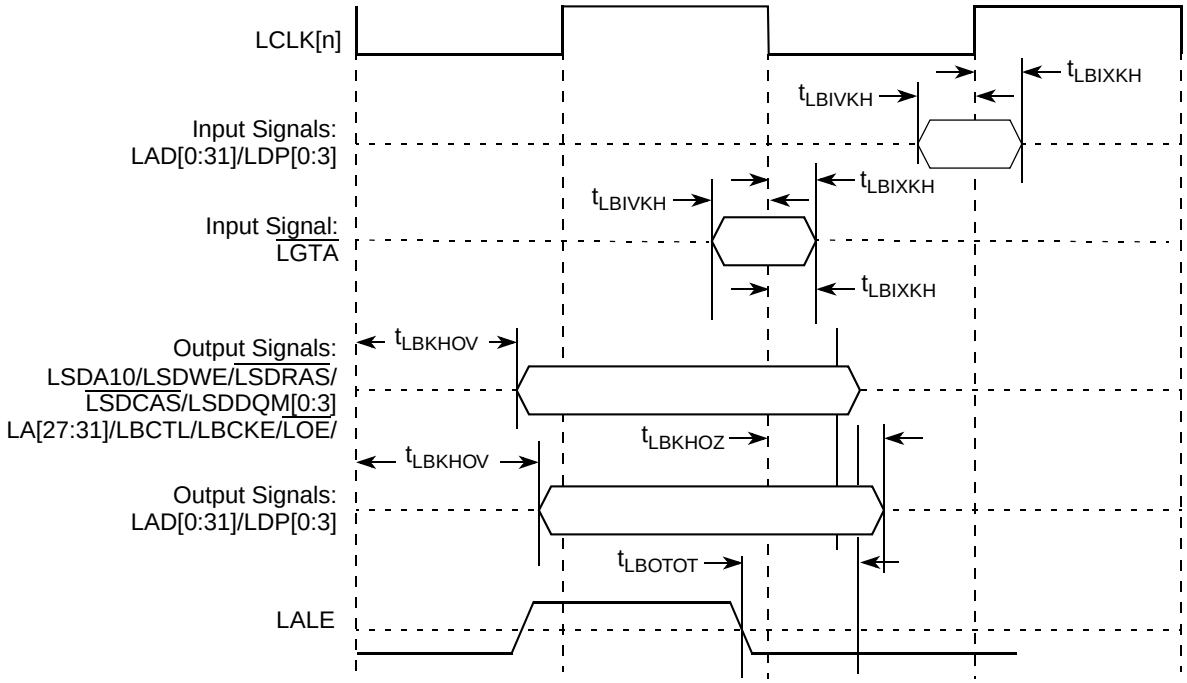


Figure 24. Local Bus Signals, Nonspecial Signals Only (DLL Bypass Mode)

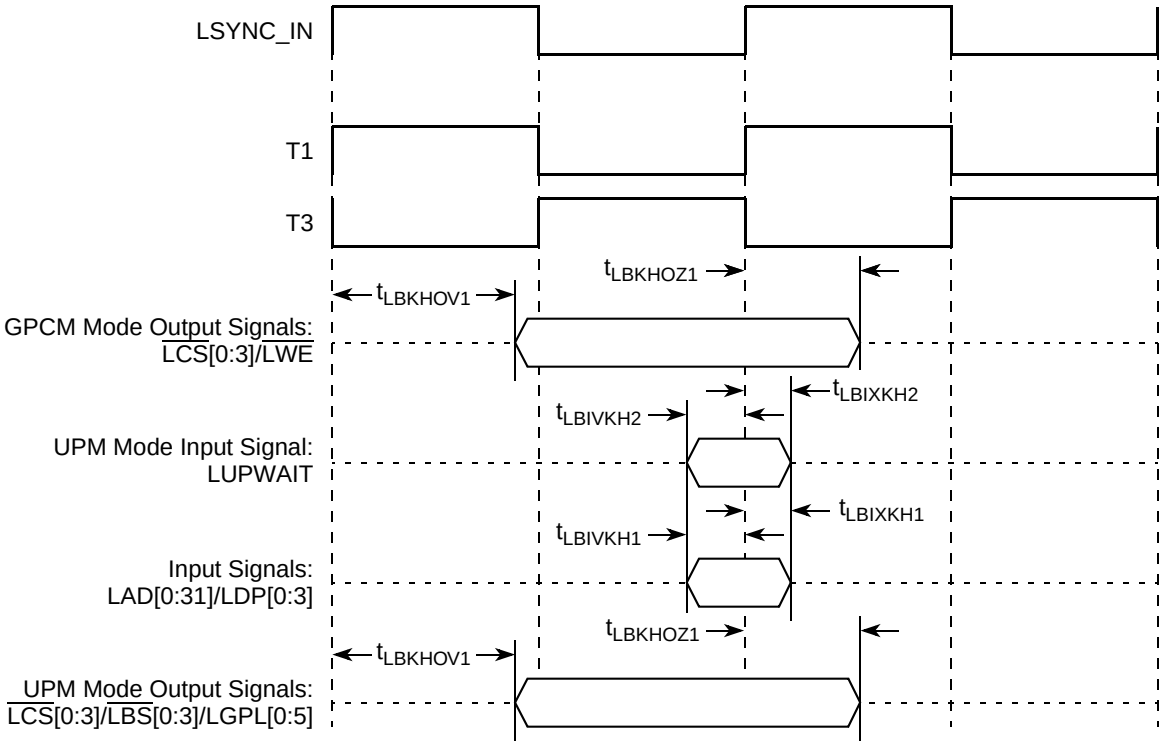


Figure 25. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 2 (DLL Enabled)

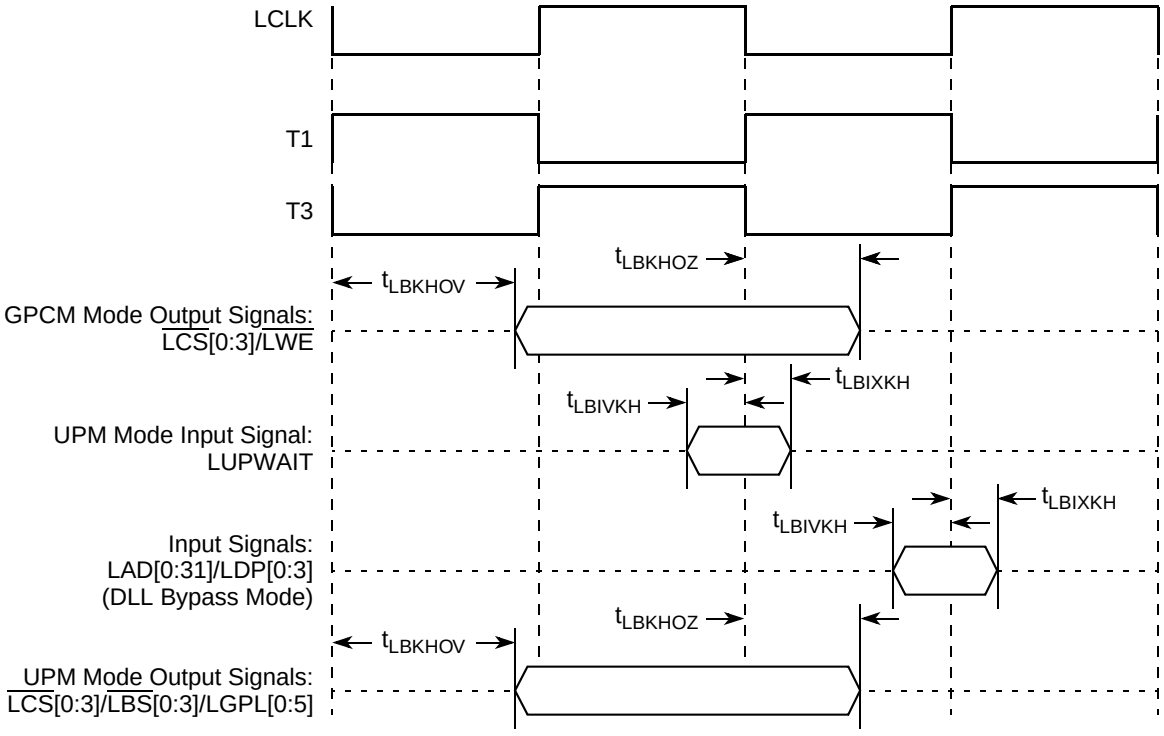


Figure 26. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 2 (DLL Bypass Mode)

10.2 JTAG AC Electrical Characteristics

This section describes the AC electrical specifications for the IEEE 1149.1 (JTAG) interface of the device.

This table provides the JTAG AC timing specifications as defined in Figure 30 through Figure 33.

Table 43. JTAG AC Timing Specifications (Independent of CLKIN)[1]

At recommended operating conditions (see Table 2).

Parameter	Symbol [2]	Min	Max	Unit	Notes
JTAG external clock frequency of operation	f_{JTG}	0	33.3	MHz	—
JTAG external clock cycle time	t_{JTG}	30	—	ns	—
JTAG external clock duty cycle	t_{JTKHKL}/t_{JTG}	45	55	%	—
JTAG external clock rise and fall times	t_{JTGR} & t_{JTGF}	0	2	ns	—
$\overline{\text{TRST}}$ assert time	t_{TRST}	25	—	ns	3
Input setup times: Boundary-scan data TMS, TDI	 t_{JTDVKH} t_{JTIVKH}	 4 4	 — —	ns	4
Input hold times: Boundary-scan data TMS, TDI	 t_{JTDXKH} t_{JTIXKH}	 10 10	 — —	ns	4
Valid times: Boundary-scan data TDO	 t_{JTKLDV} t_{JTKLOV}	 2 2	 11 11	ns	5
Output hold times: Boundary-scan data TDO	 t_{JTKLDX} t_{JTKLOX}	 2 2	 — —	ns	5
JTAG external clock to output high impedance: Boundary-scan data TDO	 t_{JTKLDZ} t_{JTKLOZ}	 2 2	 19 9	ns	5, 6

Notes:

1. All outputs are measured from the midpoint voltage of the falling/rising edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50-Ω load (see Figure 22). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.
2. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{JTDVKH} symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, t_{JTDXKH} symbolizes JTAG timing (JT) with respect to the time data input signals (D) went invalid (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
3. $\overline{\text{TRST}}$ is an asynchronous level sensitive signal. The setup time is for test purposes only.
4. Non-JTAG signal input timing with respect to t_{TCLK}.
5. Non-JTAG signal output timing with respect to t_{TCLK}.
6. Guaranteed by design and characterization.

Table 56. SPI AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max	Unit
SPI inputs—Slave mode (external clock) input hold time	t_{NEIXKH}	2	—	ns

Notes:
1. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{NIKHOV} symbolizes the NMSI outputs internal timing (NI) for the time t_{SPI} memory clock reference (K) goes from the high state (H) until outputs (O) are valid (V).

This figure provides the AC test load for the SPI.

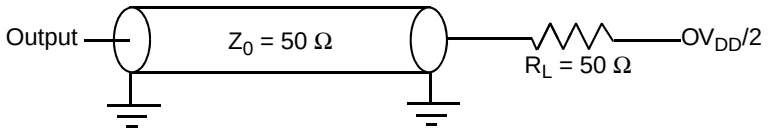
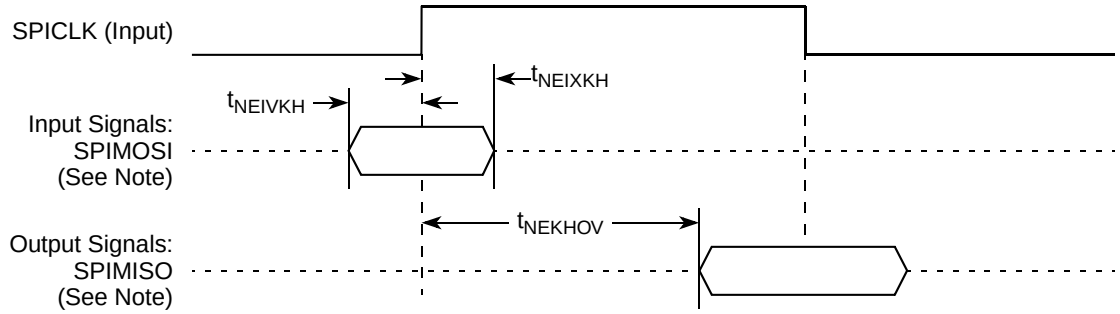


Figure 41. SPI AC Test Load

These figures represent the AC timing from Table 56. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.

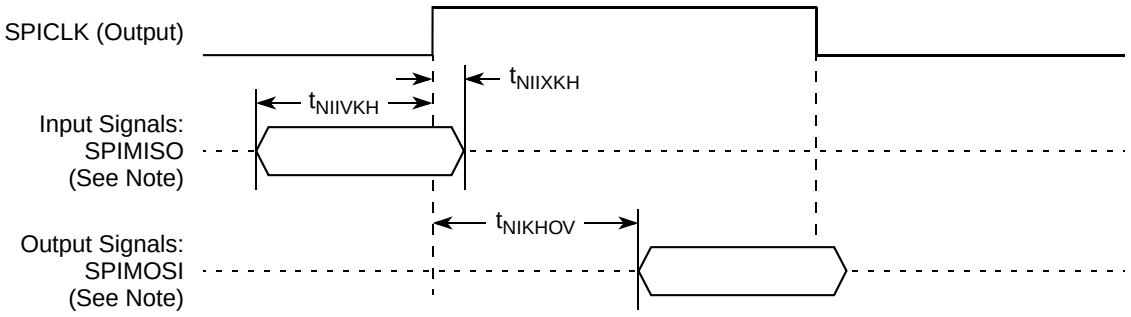
This figure shows the SPI timing in slave mode (external clock).



Note: The clock edge is selectable on SPI.

Figure 42. SPI AC Timing in Slave Mode (External Clock) Diagram

This figure shows the SPI timing in Master mode (internal clock).



Note: The clock edge is selectable on SPI.

Figure 43. SPI AC Timing in Master Mode (Internal Clock) Diagram

Table 67. MPC8358E TBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI_MODE	D36	I	OV_{DD}	—
M66EN/CE_PF[4]	B37	I/O	OV_{DD}	—
Local Bus Controller Interface				
LAD[0:31]	N32, N33, N35, N36, P37, P32, P34, R36, R35, R34, R33, T37, T35, T34, T33, U37, T32, U36, U34, V36, V35, W37, W35, V33, V32, W34, Y36, W32, AA37, Y33, AA35, AA34	I/O	OV_{DD}	—
LDP[0]/CKSTOP_OUT	AB37	I/O	OV_{DD}	—
LDP[1]/CKSTOP_IN	AB36	I/O	OV_{DD}	—
LDP[2]/LCS[6]	AB35	I/O	OV_{DD}	—
LDP[3]/LCS[7]	AA33	I/O	OV_{DD}	—
LA[27:31]	AC37, AA32, AC36, AC34, AD36	O	OV_{DD}	—
LCS[0:5]	AD33, AG37, AF34, AE33, AD32, AH37	O	OV_{DD}	—
LWE[0:3]/LSDDQM[0:3]/LBS[0:3]	AG35, AG34, AH36, AE32	O	OV_{DD}	—
LBCTL	AD35	O	OV_{DD}	—
LALE	M37	O	OV_{DD}	—
LGPL0/LSDA10/cfg_reset_source0	AB32	I/O	OV_{DD}	—
LGPL1/LSDWE/cfg_reset_source1	AE37	I/O	OV_{DD}	—
LGPL2/LSDRAS/LOE	AC33	O	OV_{DD}	—
LGPL3/LSDCAS/cfg_reset_source2	AD34	I/O	OV_{DD}	—
LGPL4/LGTA/LUPWAIT/LPBSE	AE35	I/O	OV_{DD}	—
LGPL5/cfg_clkin_div	AF36	I/O	OV_{DD}	—
LCKE	G36	O	OV_{DD}	—
LCLK[0]	J33	O	OV_{DD}	—
LCLK[1]/LCS[6]	J34	O	OV_{DD}	—
LCLK[2]/LCS[7]	G37	O	OV_{DD}	—
LSYNC_OUT	F34	O	OV_{DD}	—
LSYNC_IN	G35	I	OV_{DD}	—
Programmable Interrupt Controller				
MCP_OUT	E34	O	OV_{DD}	2
IRQ0/MCP_IN	C37	I	OV_{DD}	—
IRQ[1]/M1SRCID[4]/M2SRCID[4]/ LSRCID[4]	F35	I/O	OV_{DD}	—
IRQ[2]/M1DVAL/M2DVAL/LDVAL	F36	I/O	OV_{DD}	—
IRQ[3]/CORE_SRESET	H34	I/O	OV_{DD}	—

Table 67. MPC8358E TBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
CE_PB[0:27]	AE2, AE1, AD5, AD3, AD2, AC6, AC5, AC4, AC2, AC1, AB5, AB4, AB3, AB1, AA6, AA4, AA2, Y6, Y4, Y3, Y2, Y1, W6, W5, W2, V5, V3, V2	I/O	OV_{DD}	—
CE_PC[0:1]	V1, U6	I/O	OV_{DD}	
CE_PC[2:3]	C16, A15	I/O	$LV_{DD}1$	—
CE_PC[4:6]	U4, U3, T6	I/O	OV_{DD}	—
CE_PC[7]	C19	I/O	$LV_{DD}2$	—
CE_PC[8:9]	A4, C5	I/O	$LV_{DD}0$	—
CE_PC[10:30]	T5, T4, T2, T1, R5, R3, R1, C11, D12, F13, B10, C10, E12, A9, B8, D10, A14, E15, B14, D15, AH2	I/O	OV_{DD}	—
CE_PD[0:27]	E11, D9, C8, F11, A7, E9, C7, A6, F10, B6, D7, E8, B5, A5, C2, E4, F5, B1, D2, G5, D1, E2, H6, F3, E1, F2, G3, H4	I/O	OV_{DD}	—
CE_PE[0:31]	K3, J2, F1, G2, J5, H3, G1, H2, K6, J3, K5, K4, L6, P6, P4, P3, P1, N4, N5, N2, N1, M2, M3, M5, M6, L1, L2, L4, E14, C13, C14, B13	I/O	OV_{DD}	—
CE_PF[0:3]	F14, D13, A12, A11	I/O	OV_{DD}	—
Clocks				
PCI_CLK_OUT[0]/CE_PF[26]	B22	I/O	$LV_{DD}2$	—
PCI_CLK_OUT[1:2]/CE_PF[27:28]	D22, A23	I/O	OV_{DD}	—
CLKIN	E37	I	OV_{DD}	—
PCI_CLOCK/PCI_SYNC_IN	M36	I	OV_{DD}	—
PCI_SYNC_OUT/CE_PF[29]	D37	I/O	OV_{DD}	3
JTAG				
TCK	K33	I	OV_{DD}	—
TDI	K34	I	OV_{DD}	4
TDO	H37	O	OV_{DD}	3
TMS	J36	I	OV_{DD}	4
$\overline{\text{TRST}}$	L32	I	OV_{DD}	4
Test				
TEST	L35	I	OV_{DD}	7
$\overline{\text{TEST\_SEL}}$	AU34	I	GV_{DD}	10
PMC				
$\overline{\text{QUIESCE}}$	B36	O	OV_{DD}	—
System Control				

Table 72. CSB Frequency Options (continued)

CFG_CLKIN_DIV at Reset[1]	SPMF	*csb_clk*: Input Clock Ratio[2]	Input Clock Frequency (MHz)[2]			
			16.67	25	33.33	66.67
			csb_clk Frequency (MHz)			
Low	0110	6:1	100	150	200	
Low	0111	7:1	116	175	233	
Low	1000	8:1	133	200	266	
Low	1001	9:1	150	225	300	
Low	1010	10:1	166	250	333	
Low	1011	11:1	183	275		
Low	1100	12:1	200	300		
Low	1101	13:1	216	325		
Low	1110	14:1	233			
Low	1111	15:1	250			
Low	0000	16:1	266			
High	0010	2:1				133
High	0011	3:1			100	200
High	0100	4:1			133	266
High	0101	5:1			166	333
High	0110	6:1			200	
High	0111	7:1			233	
High	1000	8:1				
High	1001	9:1				
High	1010	10:1				
High	1011	11:1				
High	1100	12:1				
High	1101	13:1				
High	1110	14:1				
High	1111	15:1				
High	0000	16:1				

1 CFG_CLKIN_DIV is only used for host mode; CLKIN must be tied low and CFG_CLKIN_DIV must be pulled down (low) in agent mode.

2 CLKIN is the input clock in host mode; PCI_CLK is the input clock in agent mode.

Table 74. QUICC Engine Block PLL Multiplication Factors (continued)

RCWL[CEPMF]	RCWL[CEPDF]	QUICC Engine PLL Multiplication Factor = RCWL[CEPMF]/ (1 + RCWL[CEPDF])
11101	0	× 29
11110	0	× 30
11111	0	× 31
00011	1	× 1.5
00101	1	× 2.5
00111	1	× 3.5
01001	1	× 4.5
01011	1	× 5.5
01101	1	× 6.5
01111	1	× 7.5
10001	1	× 8.5
10011	1	× 9.5
10101	1	× 10.5
10111	1	× 11.5
11001	1	× 12.5
11011	1	× 13.5
11101	1	× 14.5

Note:
1. Reserved modes are not listed.

The RCWL[CEVCOD] denotes the QUICC Engine Block PLL VCO internal frequency as shown in this table.

Table 75. QUICC Engine Block PLL VCO Divider

RCWL[CEVCOD]	VCO Divider
00	4
01	8
10	2
11	Reserved

NOTE

The VCO divider (RCWL[CEVCOD]) must be set properly so that the QUICC Engine block VCO frequency is in the range of 600–1400 MHz. The QUICC Engine block frequency is not restricted by the CSB and core frequencies. The CSB, core, and QUICC Engine block frequencies should be selected according to the performance requirements.

This table shows heat sinks and junction-to-ambient thermal resistance for TBGA package.

Table 78. Heat Sinks and Junction-to-Ambient Thermal Resistance of TBGA Package

Heat Sink Assuming Thermal Grease	Airflow	35 × 35 mm TBGA
		Junction-to-Ambient Thermal Resistance
AAVID 30 × 30 × 9.4 mm pin fin	Natural convention	10.7
AAVID 30 × 30 × 9.4 mm pin fin	1 m/s	6.2
AAVID 30 × 30 × 9.4 mm pin fin	2 m/s	5.3
AAVID 31 × 35 × 23 mm pin fin	Natural convention	8.1
AAVID 31 × 35 × 23 mm pin fin	1 m/s	4.4
AAVID 31 × 35 × 23 mm pin fin	2 m/s	3.7
Wakefield, 53 × 53 × 25 mm pin fin	Natural convention	5.4
Wakefield, 53 × 53 × 25 mm pin fin	1 m/s	3.2
Wakefield, 53 × 53 × 25 mm pin fin	2 m/s	2.4
MEI, 75 × 85 × 12 no adjacent board, extrusion	Natural convention	6.4
MEI, 75 × 85 × 12 no adjacent board, extrusion	1 m/s	3.8
MEI, 75 × 85 × 12 no adjacent board, extrusion	2 m/s	2.5
MEI, 75 × 85 × 12 mm, adjacent board, 40 mm side bypass	1 m/s	2.8

Accurate thermal design requires thermal modeling of the application environment using computational fluid dynamics software which can model both the conduction cooling and the convection cooling of the air moving through the application. Simplified thermal models of the packages can be assembled using the junction-to-case and junction-to-board thermal resistances listed in the thermal resistance table. More detailed thermal models can be made available on request.

Heat sink vendors include the following:

Aavid Thermalloy 603-224-9988
80 Commercial St.
Concord, NH 03301
Internet: www.aavidthermalloy.com

Alpha Novatech 408-749-7601
473 Sapena Ct. #15
Santa Clara, CA 95054
Internet: www.alphanovatech.com

International Electronic Research Corporation (IERC) 818-842-7277
413 North Moss St.
Burbank, CA 91502
Internet: www.ctscorp.com

23.7 Pull-Up Resistor Requirements

The device requires high resistance pull-up resistors (10 kΩ is recommended) on open drain type pins including I^2C pins, Ethernet Management MDIO pin, and EPIC interrupt pins.

For more information on required pull-up resistors and the connections required for the JTAG interface, see *MPC8360E/MPC8358E PowerQUICC Design Checklist* (AN3097).

24 Ordering Information

24.1 Part Numbers Fully Addressed by this Document

This table provides the Freescale part numbering nomenclature for the MPC8360E/58E. Note that the individual part numbers correspond to a maximum processor core frequency. For available frequencies, contact your local Freescale sales office. Additionally to the processor frequency, the part numbering scheme also includes an application modifier, which may specify special application conditions. Each part number also contains a revision code that refers to the die mask revision number.

Table 80. Part Numbering Nomenclature[1]

MPC	***nnnn***	***e***	***t***	***pp***	***aa***	***a***	***a***	***A***
Product Code	**Part Identifier**	**Encryption Acceleration**	**Temperature Range**	**Package[2]**	**Processor Frequency[3]**	**Platform Frequency**	**QUICC Engine Frequency**	**Die Revision**
MPC	8358	Blank = not included E = included	Blank = 0° C T_A to 105° C T_J C= –40° C T_A to 105° C T_J	ZU = TBGA VV = TBGA (no lead)	e300 core speed AD = 266 MHz AG = 400 MHz	D = 266 MHz	E = 300 MHz G = 400 MHz	A = rev. 2.1 silicon
	8360				e300 core speed AG = 400 MHz AJ = 533 MHz AL = 667 MHz	D = 266 MHz F = 333 MHz	G = 400 MHz H = 500 MHz	A = rev. 2.1 silicon
MPC (rev. 2.0 silicon only)	8360	Blank = not included E = included	0° C T_A to 70° C T_J	ZU = TBGA VV = TBGA (no lead)	e300 core speed AH = 500 MHz AL = 667 MHz	F = 333 MHz	G = 400 MHz H = 500 MHz	—

Notes:

1. Not all processor, platform, and QUICC Engine block frequency combinations are supported. For available frequency combinations, contact your local Freescale sales office or authorized distributor.
2. See Section 20, "Package and Pin Listings," for more information on available package types.
3. Processor core frequencies supported by parts addressed by this specification only. Not all parts described in this specification support all core frequencies. Additionally, parts addressed by part number specifications may support other maximum core frequencies.

This table shows the SVR settings by device and package type.

Table 81. SVR Settings

Device	Package	SVR (Rev. 2.0)	SVR (Rev. 2.1)
MPC8360E	TBGA	0x8048_0020	0x8048_0021
MPC8360	TBGA	0x8049_0020	0x8049_0021